

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	34	semiconductor and ESD and (deep near3 well) and (second near3 well) and ((source near4 connect\$3) near4 drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/02 21:46
L2	244	semiconductor and ESD and (second near3 well) and ((source near4 connect\$3) near4 drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/02 22:43
L3	224	semiconductor and ESD and (second near3 well) and ((source near4 connect\$3) near4 drain) and @ad<"20031223"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/02 21:51
L4	495	257/173.ccls. and @ad<"20031223"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/02 22:35
L6	1845	(257/355 or 257/357).ccls. and @ad<"20031223"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/02 22:04
L7	237	(257/355 or 257/357).ccls. and @ad<"20031223" and ((common or shar\$4) with (drain or source))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/02 22:31
L8	175	(257/360 or 257/361).ccls. and @ad<"20031223" and ((common or shar\$4) with (drain or source))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/02 22:31
L9	42	(257/546 or 257/547).ccls. and @ad<"20031223" and ((common or shar\$4) with (drain or source))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/02 22:24
L10	598	(257/546 or 257/547).ccls. and @ad<"20031223"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/02 22:25
L11	25	(257/566).ccls. and @ad<"20031223" and ((common or shar\$4) with (drain or source))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/02 22:23

L12	232	(257/566).ccls. and @ad<"20031223"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/02 22:23
L13	263	(257/566).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/02 22:23
L14	31	(257/566).ccls. not L12	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/02 22:23
L15	0	(257/546 or 257/547).ccls. and ((common or shar\$4) with (drain or source)) not L9	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/02 22:24
L16	5	(257/546 or 257/547).ccls. not L10	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/02 22:24
L17	603	(257/546 or 257/547).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/02 22:25
L18	179	(257/360 or 257/361).ccls. and ((common or shar\$4) with (drain or source))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/02 22:31
L19	252	(257/355 or 257/357).ccls. and ((common or shar\$4) with (drain or source))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/02 22:31
L20	505	257/173.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/02 22:35
L21	187	semiconductor and ESD and (second near3 well) and ((common or shar\$4) with (drain or source))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/02 22:44